

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/332,271
Priority Filing Date June 11, 1999
Inventor Klaus Florian Schuegraf et al.
Assignee Micron Technology, Inc.
Priority Group Art Unit 2815
Priority Examiner E. Lee
Attorney's Docket No. MI22-1741
Title: Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects,
and Wordline, Transistor Gate, and Conductive Interconnect Structures

PRELIMINARY AMENDMENT

To: Assistant Commissioner for Patents
Washington, D.C. 20231

From: D. Brent Kenady (Tel. 509-624-4276; Fax 509-838-3424)
Wells, St. John, Roberts, Gregory & Matkin P.S.
601 W. First Avenue, Suite 1300
Spokane, WA 99201-3828

AMENDMENTS**In the Specification**

At page 1, before the "Technical Field" section, insert the following paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

--RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/332,271, filed June 11, 1999.--.

In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

CLAIMS

Please cancel claims 1-20.

21. A conductive line comprising:
 - a polysilicon layer; and
 - a metal-silicide layer against the layer of polysilicon, the metal-silicide layer comprising a Group III dopant or a Group V dopant.
22. The conductive line of claim 21 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1×10^{18} ions/cm³.
23. A metal-silicide layer comprising a Group III dopant or a Group V dopant.
24. The metal-silicide of claim 23 comprising a concentration of the dopant of at least about 1×10^{18} ions/cm³.

25. A programmable-read-only-memory device comprising:
a first dielectric layer over a substrate;
a floating gate over the first dielectric layer;
a second dielectric layer over the floating gate;
a conductive line over the second dielectric layer; and
a metal-silicide layer over the conductive line, the metal-silicide layer
comprising a Group III dopant or a Group V dopant.

26. The programmable-read-only-memory device of claim 25 wherein the
device is an EPROM.

27. The programmable-read-only-memory device of claim 25 wherein the
device is an EEPROM.

28. The programmable-read-only-memory device of claim 25 wherein the
metal-silicide layer comprises a concentration of the dopant of at least
about 1×10^{18} ions/cm³.

REMARKS

Claims 1-20 are canceled. Claims 21-28 are pending in the application, and Applicant requests examination of such pending claims.

The signature of Klaus Florian Schuegraf is missing from the filed declaration as an "uncooperative inventor". Accordingly, this application is filed with an attached granted Petition pursuant to 37 C.F.R. §1.47(a) due to an "uncooperative inventor" and a declaration signed by the cooperative inventor. The enclosed granted Petition under §1.47(a) is from the parent file (U.S. Patent Application Serial No. 09/332,271).

Respectfully submitted,

Dated: 6-4-01

By: 
D. Brent Kenady
Reg. No. 40,045

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
PRELIMINARY AMENDMENT**

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

At page 1, before the "Technical Field" section, insert the following paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

--RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/332,271, filed June 11, 1999.--.

In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Please cancel claims 1-20.